

Application Serial No. 09/817,567
Attorney Docket No. 060879-0006
(formerly 11299-006-999)

Amendments to the Specification:

Please amend the specification as follows::

Page 5, fifth paragraph

FIG. 1D is a sectional view illustrating a fourth step in the method of constructing the lancet device with the nitride film 16d14d and the photoresist 16d being etched away leaving strips of uncovered bare silicon wafer;

Page 5, seventh paragraph

FIG. 1F is a sectional view illustrating the method of constructing the lancet device in accordance with the present invention with ~~approximately 50 micrometers and approximately 100 micrometers areas of thinned silicon wafer~~ being exposed after the fifth step;

Page 7, third paragraph

As illustrated in **FIG. 1E**, the uncovered areas of the silicon wafer 12e are etched away in bulk by potassium hydroxide (KOH). Etching the silicon wafer 12e with potassium hydroxide results in between ~~approximately 50 micrometers and approximately 100 micrometers of the silicon wafer 12e areas of thinned silicon wafer~~ being exposed, as illustrated in **FIG. 1F**. Next, as illustrated in **FIG. 1G**, a photoresist coating 18g is applied to the silicon wafer 12g. Then, as illustrated in **FIG. 1H**, the silicon wafer 12h is patterned and exposed and the lancet devices 10h are “punched” out using a plasma etching process. Plasma etching provides excellent control of the shape of the microlancet without forming weak spots. Finally, as illustrated in **FIG. 1I**, the photoresist coating 18h is removed resulting in a silicon lancet device with a nitride-covered base.

Page 8, third paragraph, Page 9, first paragraph

Disposable microlancet device 30i (see **FIG. 3A**) may be employed for obtaining a blood sample through the skin of a subject. The device is formed by an elongated single crystal silicon substrate 32a having base end 30b and penetration end 30p. Base portion 32b formed at the base end of the silicon substrate permits the device to be retained during penetration and sampling. Penetration portion 32p formed at the penetration end has smooth continuous profile and terminates in a sharp point with smooth continuous cutting profile.

508197-1

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The smooth profile permits easy piercing and penetration of the skin in order to obtain a blood sample while inflicting minimum pain on the subject. The penetration portion has a thickness cross-section dimension "T" (see FIG.s 3B and 3C) and a width cross section dimension "W" (see FIG.s 3A and 3C). The cross-section may be any suitable shape such as rhombic or rectangular as shown in FIG. 3C. The thickness dimension T of the base portion may extend from about 50 micrometers to about 250 micrometers ~~excluding the sharp point~~. The width dimension W of the base portion may extend from about 50 micrometers to about 250 micrometers excluding the point. At least one of these dimensions may taper toward the penetration end to form the ~~sharp~~ point (see FIG. 3A). The silicon substrate may have a length diameter 'L' (see FIG. 3B) of about 1 millimeter to about 3 millimeters, Silicon nitride film 34 may extend over at least part of the base portion.

508197-1

3 of 9